

# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										備考	
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>FE</sub> h <sub>FE</sub> * (Ω)	h <sub>FE</sub> h <sub>FE</sub> * (×10 <sup>-4</sup> )	h <sub>FE</sub> h <sub>FE</sub> * (μS)	f <sub>αb</sub> f <sub>r</sub> * (Mc)		C <sub>ob</sub> (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
  - 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
  - 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
  - 11 OUTLINE
  - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)													外形	備考						
				V <sub>CEO</sub> (V)	V <sub>EB0</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CEO</sub> 最大値 (μA)	V <sub>CE</sub> (V)	直流又はパルス h <sub>FE</sub>	バイアス	V <sub>CE</sub> (V)	I <sub>E</sub> (mA)	h <sub>FE</sub>	h <sub>ie</sub> h <sub>ie</sub> * (Ω)	h <sub>re</sub> h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>oe</sub> * (μΩ)	f <sub>αB</sub> f <sub>T</sub> * (Mc)	C <sub>ob</sub> (pF)	r <sub>bb</sub> h <sub>ie</sub> (real)* (Ω)								
2SC1811	ソニー	RF	Si.E	240	5	100	750	120	0.2	100	150	5	3	10	-20	h <sub>ie</sub> = 8dB (f=100MHz)									2.4	C <sub>ob</sub> = 7.5pF 45pS	259	2SA896 とコンパリ	
" 1812	"	"	"	22	3	20	210	100	0.2	15	80	10	3	10	-3	NF=3.7dB (f=800MHz, V <sub>CE</sub> =10V, I <sub>C</sub> =3mA)								1100*	0.75	C <sub>ob</sub> = 3.5pS	305A	フェワード AGC	
" 1813	"	"	Si.E PaMe	50	5	500	500	120	0.2	49	200	2	100	10	-10									100*	8	C <sub>ob</sub> = 110pS	138D		
" 1814																													
" 1815	東芝	AF	Si.E	60	5	150	400	125	0.1	60	70~700	6	2	10	-1	NF=1dB (f=1kHz, 6V, 0.1mA)								>80*	2	50	138	2SA1015 とコンパリ	
" 1816	ソニー	RF. PA	Si.E PaMe	100	6	4A	16W (T <sub>C</sub> =25°C)	150	1	50	100	2	100	10	-100	P <sub>o</sub> = 6W (f=27MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =0.4W)								140*	45	C <sub>ob</sub> = 36pS	268		
" 1817	"	PA	Si.E	45	4	5A	25W (T <sub>C</sub> =25°C)	150	2	40	60	2	100	10	-1A	P <sub>o</sub> = 20W (f=27MHz, V <sub>CE</sub> =12V, P <sub>i</sub> =1W)								250*	80		268		
* " 1818	松下	PA	Si.EMe	130	5	7A	100W (T <sub>C</sub> =25°C)	150	500	70	150	5	7A	10	-500									7*	400	10	102		
" 1819	"	"	Si.TP	300	5	100	15W (T <sub>C</sub> =25°C)	150	10	300	100	10	30	30	-20									100*	4.5	15	268		
" 1820	富士通	RF. PA	Si.EP	55	3.5	500	3W (T <sub>C</sub> =25°C)	175	100	20	50	5	200			P <sub>o</sub> = 1.6W (f=175MHz)									4		84B		
" 1821	"	"	"	55	3.5	500	7W (T <sub>C</sub> =25°C)	175	100	20	50	5	200			P <sub>o</sub> = 4W (f=470MHz)									4.5		246		
" 1822	"	"	"	55	3.5	1A	12W (T <sub>C</sub> =25°C)	175	200	20	50	5	500			P <sub>o</sub> = 7.5W (f=470MHz)									7		246		
" 1823	"	"	"	55	3.5	2A	25W (T <sub>C</sub> =25°C)	175	400	20	50	5	1A			P <sub>o</sub> = 15W (f=470MHz)									12		246		
" 1824	"	"	"	55	3.5	4A	40W (T <sub>C</sub> =25°C)	175	800	20	50	5	3A			P <sub>o</sub> = 30W (f=470MHz)									23		246		
" 1825	"	"	"	55	3.5	8A	75W (T <sub>C</sub> =25°C)	175	1.6mA	20	50	5	6A			P <sub>o</sub> = 55W (f=470MHz)									45				
" 1826	サンケン	PA	Si.TMe	80	6	4A	30W (T <sub>C</sub> =25°C)	150	1mA	80	100	4	1A	12	-200									10*	40	20*	298		
" 1827	"	"	"	100	6	4A	30W (T <sub>C</sub> =25°C)	150	1mA	100	100	4	1A	12	-200									10*	40	20*	298		
" 1828	"	"	"	800	6	1A	40W (T <sub>C</sub> =25°C)	150	100	800	70	10	200	10	-100									7*	20	12*	99		
" 1829	"	"	"	200	6	5A	100W (T <sub>C</sub> =25°C)	150	1mA	200	1000	4	1A	12	-500									15*	50	100*	102		
" 1830	"	"	"	140	7	15A	150W (T <sub>C</sub> =25°C)	150	100	140	>500	2	8A	12	-500									10*			102	ゲーリントン	
" 1831	"	"	"	90	6	8A	100W (T <sub>C</sub> =25°C)	150	1mA	90	1000	4	1A	12	-500									10*	100	40*	102	ゲーリントン	
" 1832	"	"	"	500	6	15A	150W (T <sub>C</sub> =25°C)	150	100	500	300	2	10A	12	-500									7*	130	40*	102	ゲーリントン	
" 1833	日電	RF.SW	Si.E	60	8	200	300	150	0.1	40	160	1	10	10	-10	t <sub>on</sub> = 45nS, t <sub>off</sub> = 250nS t <sub>ring</sub> = 190nS								300*	3.5		138		
" 1834	"	"	"	40	5	200	300	150	0.1	30	120	1	10	10	-10	t <sub>on</sub> < 20nS, t <sub>off</sub> < 40nS t <sub>ring</sub> < 20nS								500*	4	120	138		
" 1835																													
" 1836																													
* " 1837	富士通	PA	Si.EP	35	3.5	600	7.5W (T <sub>C</sub> =25°C)	175	400	20	50	5	200			P <sub>o</sub> = 1W (f=2GHz, V <sub>CE</sub> =18V, P <sub>i</sub> =0.2W)												166	
* " 1838	"	"	"	35	3.5	1.5A	15W (T <sub>C</sub> =25°C)	175	1mA	20	50	5	500			P <sub>o</sub> = 3W (f=2GHz, V <sub>CE</sub> =18V, P <sub>i</sub> =1W)												166	
" 1839																													
" 1840	日電	AF	Si.E	40	5	100	500	125	0.05	40	400	6	1	6	-1									100*	< 8		138		